ABSTRACT OF THE DISCLOSURE

Provided is a suitable cleaning method of porous semiconductor substrate without occurrence of collapse of porous structure due to cavitation or resonance.

In a cleaning method of porous surface of semiconductor substrate having the porous structure at least in the surface, cleaning for removing dust particles adhering to the porous surface of the substrate takes place with pure water on which a high-frequency wave with a frequency in the range of from 600 kHz to 2 MHz is superimposed.